
2SK2569

Silicon N-Channel MOS FET

HITACHI

ADE-208-384
1st. Edition

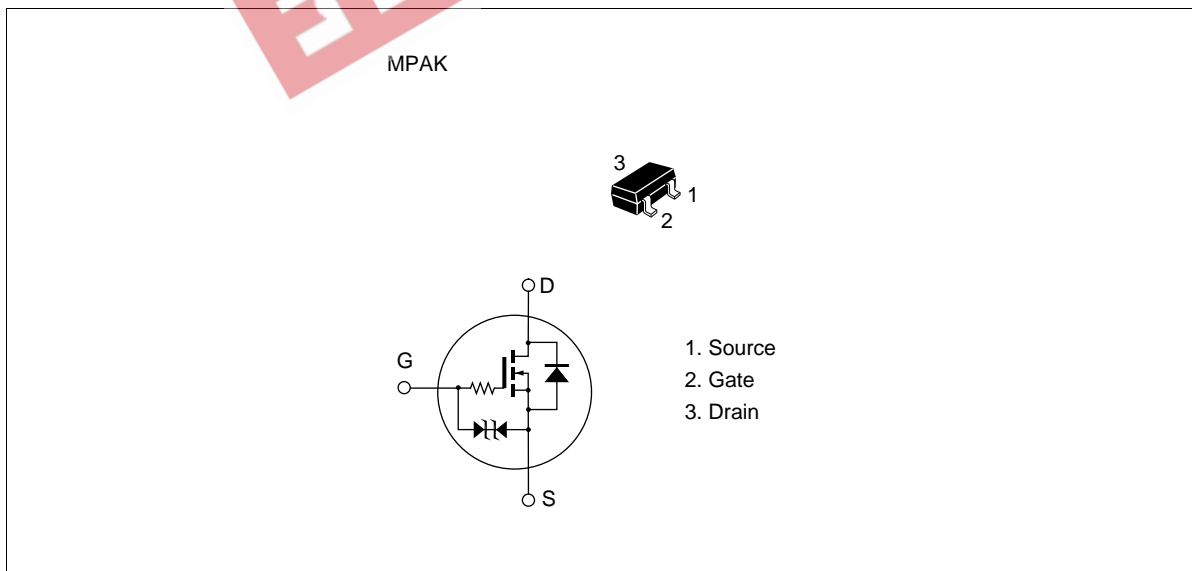
Application

Low frequency power switching

Features

- Low on-resistance.
- $R_{DS(on)} = 2.6$ max. (at $V_{GS} = 4$ V, $I_D = 100$ mA)
- 2.5V gate drive device.
- Small package (MPAK).

Outline



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Absolute Maximum Ratings (Ta = 25°C)

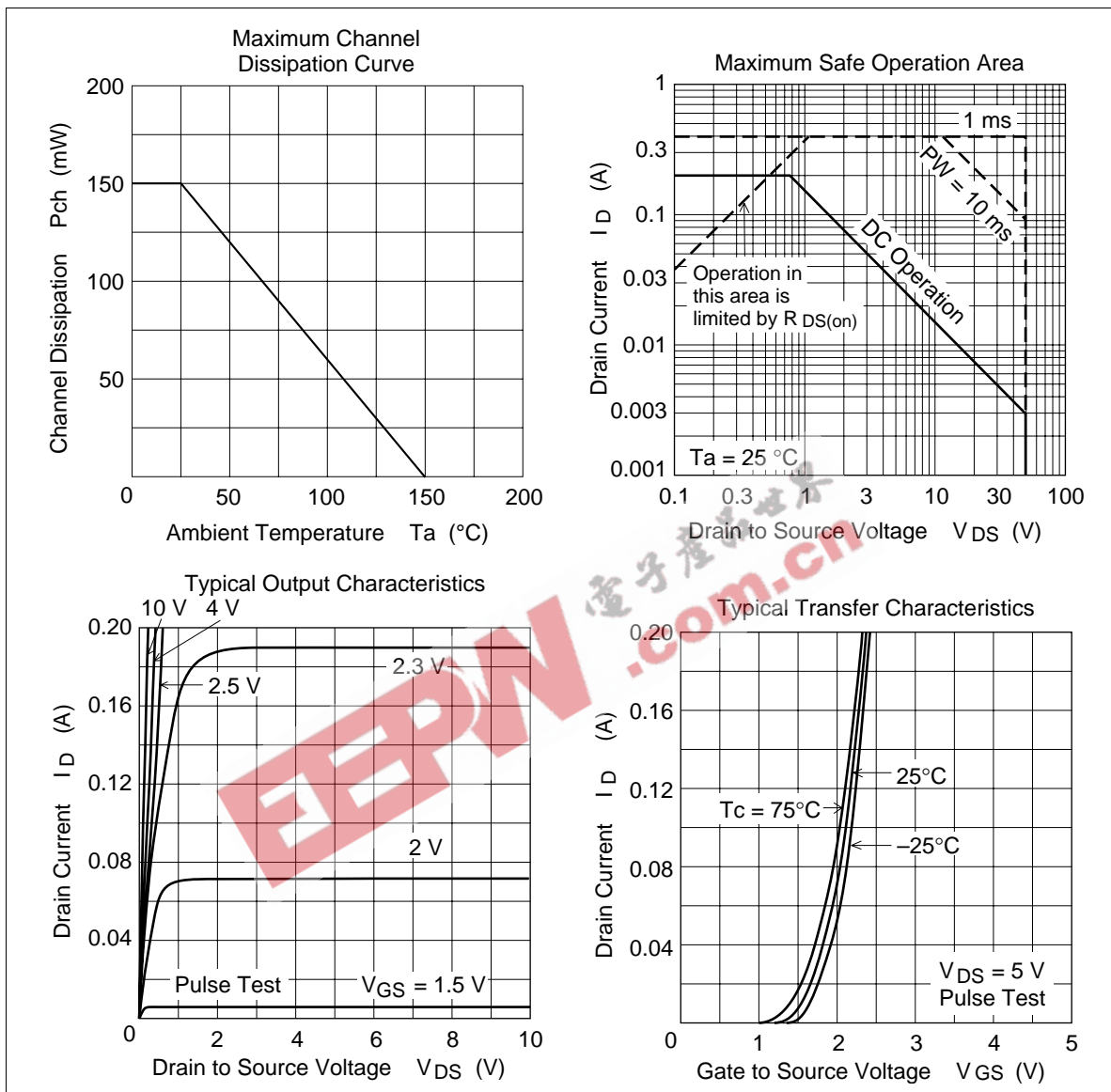
Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	50	V
Gate to source voltage	V_{GSS}	±20	V
Drain current	I_D	0.2	A
Drain peak current	$I_{D(pulse)}^{*1}$	0.4	A
Channel dissipation	Pch^{*2}	150	mW
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

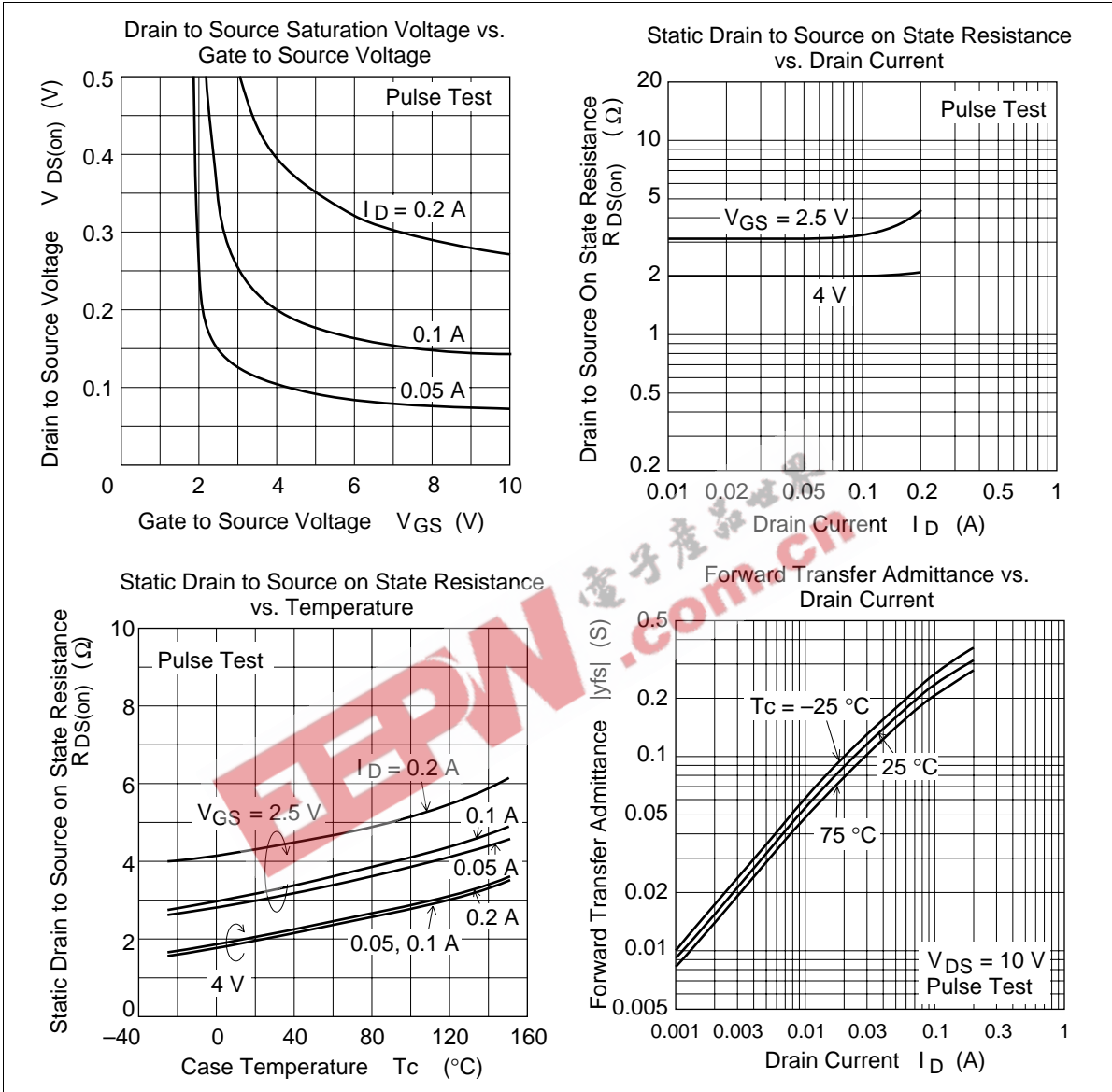
Notes 1. $PW \leq 10 \mu s$, duty cycle $\leq 1\%$

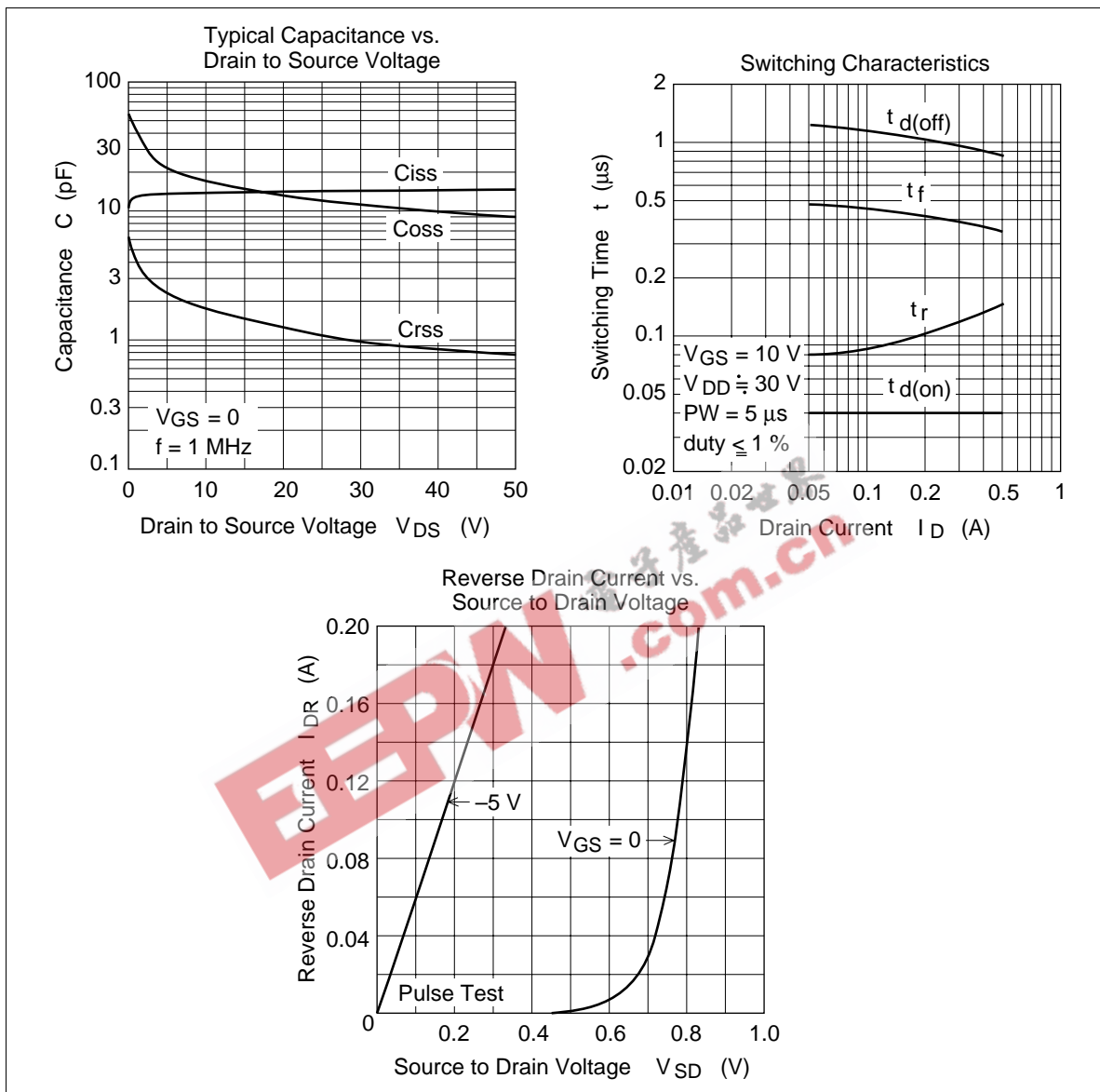
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	50	—	—	V	$I_D = 100 \mu A$, $V_{GS} = 0$
Gate to source breakdown voltage	$V_{(BR)GSS}$	±20	—	—	V	$I_G = \pm 100 \mu A$, $V_{DS} = 0$
Zero gate voltage drain current	I_{DSS}	—	—	1.0	μA	$V_{DS} = 40 V$, $V_{GS} = 0$
Gate to source leak current	I_{GSS}	—	—	±2.0	μA	$V_{GS} = \pm 16 V$, $V_{DS} = 0$
Gate to source cutoff voltage	$V_{GS(off)}$	0.5	—	1.5	V	$I_D = 10 \mu A$, $V_{DS} = 5 V$
Static drain to source on state resistance	$R_{DS(on)1}$	—	2.0	2.6	Ω	$I_D = 100 mA$ $V_{GS} = 4 V^{*1}$
Static drain to source on state resistance	$R_{DS(on)2}$	—	3.1	5.0	Ω	$I_D = 40 mA$ $V_{GS} = 2.5 V^{*1}$
Forward transfer admittance	$ y_{fs} $	0.13	0.23	—	S	$I_D = 100 mA$ $V_{DS} = 10 V$
Input capacitance	Ciss	—	14.0	—	pF	$V_{DS} = 10 V$
Output capacitance	Coss	—	17.2	—	pF	$V_{GS} = 0$
Reverse transfer capacitance	Crss	—	1.73	—	pF	$f = 1 MHz$
Turn-on delay time	$t_{d(on)}$	—	40	—	μs	$V_{GS} = 10 V$, $I_D = 100 mA$
Rise time	t_r	—	86	—	μs	$R_L = 300 \Omega$
Turn-off delay time	$t_{d(off)}$	—	1120	—	μs	
Fall time	t_f	—	430	—	μs	

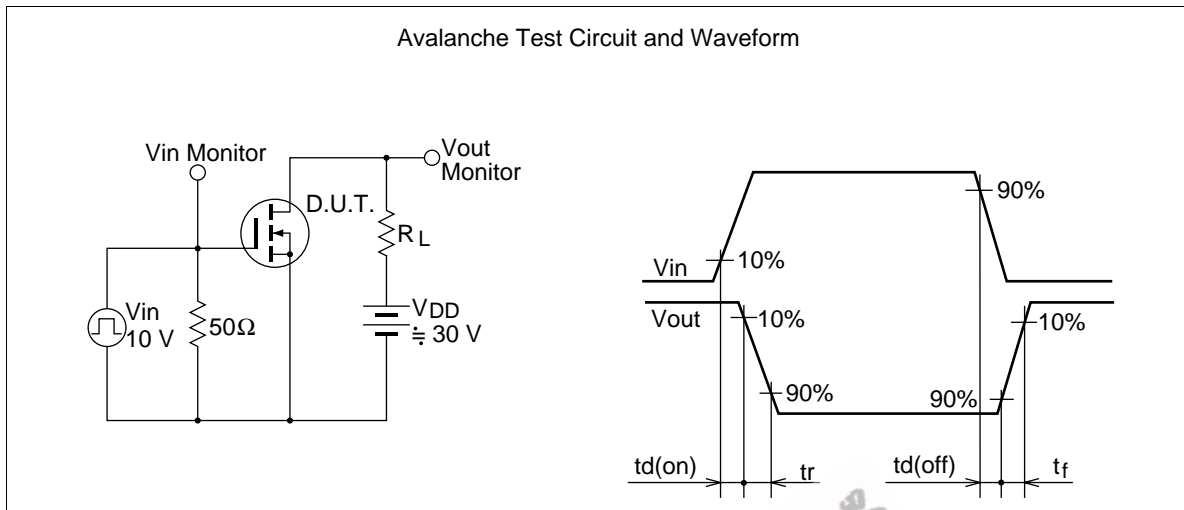
Notes 1. Pulse Test
2. Marking is "ZN—"







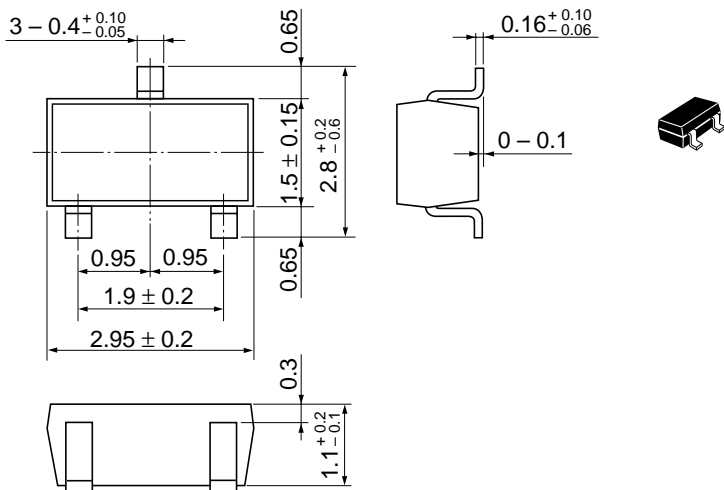
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Unit: mm



Hitachi Code	MPAK
JEDEC	—
EIAJ	Conforms
Weight (reference value)	0.011 g

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